

Features

- 600-Volt Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

Benefits

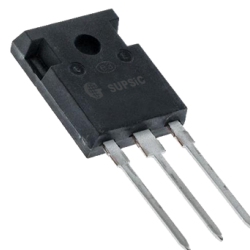
- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters

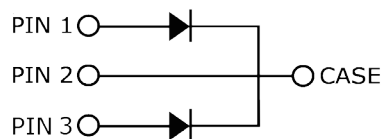
Part Number	Package	Marking
GC3D20060D	TO-247-3	GC3D20060

$$\begin{aligned}
 V_{RRM} &= 600 \text{ V} \\
 I_F (T_c=135^\circ\text{C}) &= 26 \text{ A}^{**} \\
 Q_c &= 48 \text{ nC}^{**}
 \end{aligned}$$



TO-247-3

Package



Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	600	V		
V_{RSM}	Surge Peak Reverse Voltage	600	V		
V_{DC}	DC Blocking Voltage	600	V		
I_F	Continuous Forward Current (Per Leg/Device)	27.5/55 13/26 10/20	A	$T_c=25^\circ\text{C}$ $T_c=135^\circ\text{C}$ $T_c=149^\circ\text{C}$	
I_{FRM}	Repetitive Peak Forward Surge Current	48 33	A	$T_c=25^\circ\text{C}$, $t_p = 10 \text{ ms}$, Half Sine Wave $T_c=110^\circ\text{C}$, $t_p = 10 \text{ ms}$, Half Sine Wave	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	91 72	A	$T_c=25^\circ\text{C}$, $t_p = 10 \text{ ms}$, Half Sine Wave $T_c=110^\circ\text{C}$, $t_p = 10 \text{ ms}$, Half Sine Wave	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	860 682	A	$T_c=25^\circ\text{C}$, $t_p = 10 \mu\text{s}$, Pulse $T_c=110^\circ\text{C}$, $t_p = 10 \mu\text{s}$, Pulse	
P_{tot}	Power Dissipation (Per Leg/Device)	136.5 59	W	$T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$	
dV/dt	Diode dV/dt ruggedness	200	V/ns	$V_R=0-650\text{V}$	
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		
	TO-247 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

Electrical Characteristics (Per Leg)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 2.0	1.8 2.4	V	$I_F = 10\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 10\text{ A}$ $T_J = 175^\circ\text{C}$	
I_R	Reverse Current	10 20	50 200	μA	$V_R = 600\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 600\text{ V}$ $T_J = 175^\circ\text{C}$	
Q_C	Total Capacitive Charge	24		nC	$V_R = 400\text{ V}$, $I_F = 10\text{ A}$ $di/dt = 500\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	
C	Total Capacitance	462 44 40		pF	$V_R = 0\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 200\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 400\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$	
E_C	Capacitance Stored Energy	3.6		μJ	$V_R = 400\text{ V}$	

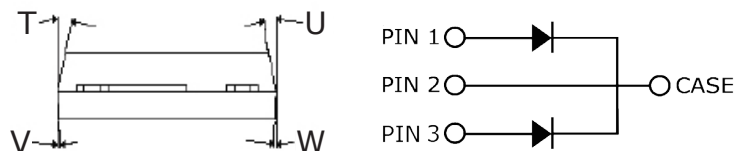
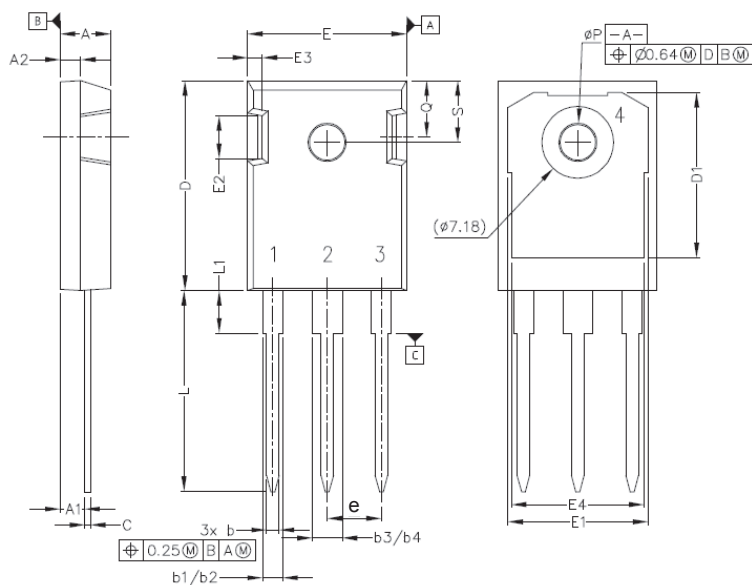
Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.3** 0.65*	$^\circ\text{C}/\text{W}$	

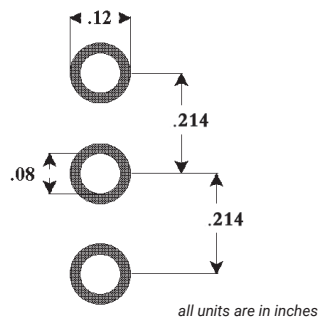
Package Dimensions

Package TO-247-3



POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.042	.052	1.07	1.33
b1	.075	.095	1.91	2.41
b2	.075	.085	1.91	2.16
b3	.113	.133	2.87	3.38
b4	.113	.123	2.87	3.13
c	.022	.027	0.55	0.68
D	.819	.831	20.80	21.10
D1	.640	.695	16.25	17.65
D2	.037	.049	0.95	1.25
E	.620	.635	15.75	16.13
E1	.516	.557	13.10	14.15
E2	.145	.201	3.68	5.10
E3	.039	.075	1.00	1.90
E4	.487	.529	12.38	13.43
e	.214 BSC		5.44 BSC	
N	3		3	
L	.780	.800	19.81	20.32
L1	.161	.173	4.10	4.40
ØP	.138	.144	3.51	3.65
Q	.216	.236	5.49	6.00
S	.238	.248	6.04	6.30
T	9°	11°	9°	11°
U	9°	11°	9°	11°
V	2°	8°	2°	8°
W	2°	8°	2°	8°

Recommended Solder Pad Layout



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GC3D20060D	TO-247-3